N-Channel MOSFET MEM2318M6

General Description

MEM2318M6 Series Dual N-channel enhancement mode field-effect transistor ,produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance. This device particularly suits low voltage applications, and low power dissipation.

Features

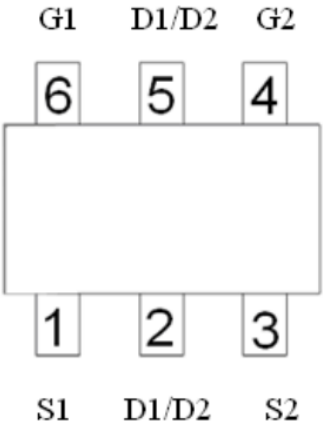
- 20V/6A

  $R_{DS(ON)}$ =16mΩ@ V_{GS}=4V,I_D=5A

  $R_{DS(ON)}$ =19mΩ@ V_{GS}=3V,I_D=4.6A

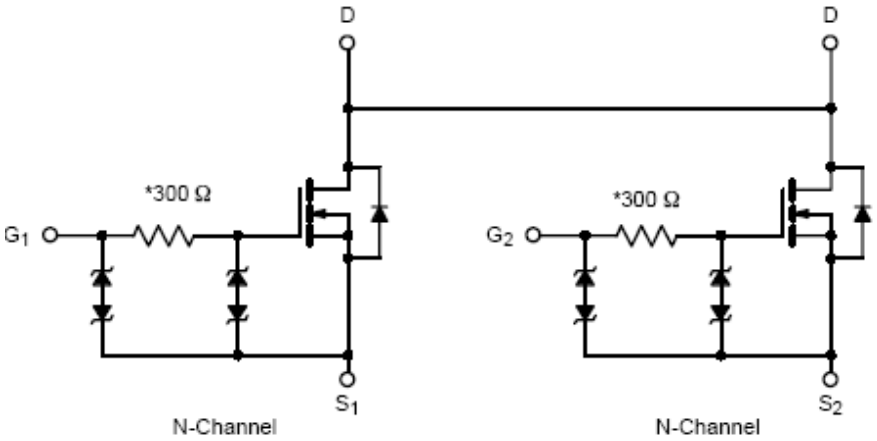
  RDS(ON) =21mΩ@VGS=2.5V,ID=4.3A
- High Density Cell Design For Ultra Low On-Resistance
- Surface mount package：SOT23-6L
- ESD Protected: 3000 V

Pin Configuration



Typical Application

- Battery management
- power management
- Portable equipment
- Low power DC to DC converter.
- Load switch
- LCD adapter



Absolute Maximum Ratings

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DSS}	20V	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current	TA=25℃	I_D	6	A
	TA=70℃		3.4	
Total Power Dissipation	TA=25℃	Pd	2	W
	TA=70℃		0.64	
Pulsed Drain Current (10us Pulse Width)		IDM	30	A
Operating Temperature Range		T_{Opr}	150	℃
Storage Temperature Range		T_{stg}	-65/150	℃

Thermal Characteristics

Parameter		Symbol	TYP.	MAX.	Unit
Thermal Resistance,Junction-to-Ambient	t≤10s	RθJA	72	83	℃/W
	Steady-State		100	120	

Electrical Characteristics

MEM2318M6

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250uA	20	24		V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250uA	0.5	0.73	1	V
Gate-Body Leakage	I_{GSS}	V_{DS}=0V， V_{GS}=12V		4.96	10	uA
		V_{DS}=0V， V_{GS}=-12V		-5.22	-10	uA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=16V V_{GS}=0V		4.91	1000	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=4V,I_D=5A		16	26.5	mΩ
		V_{GS}=3V,I_D=4.6A		19	32	mΩ
		V_{GS}=2.5V,I_D=4.3A		21	37	mΩ
Forward Transconductance	g_{FS}	V_{DS} =10 V, I_D = 6A	6	20		S
Source-drain (diode forward) voltage	V_{SD}	V_{GS}=0V,I_S=1.5A		0.7	1	V
Dynamic Characteristics						
Input Capacitance	Ciss	V_{DS} = 8 V, V_{GS} = 0 V, f = 1 MHz		1120	1500	pF
Output Capacitance	Coss			480	630	
Reverse Transfer Capacitance	Crss			110	160	

Switching Characteristics						
Turn-On Delay Time	td(on)	V_{DD} = 10 V, RL = 10Ω		25	60	ns
Rise Time	tr	I_D =1 A,		60	140	
Turn-Off Delay Time	td(off)	V_{GEN} = 4.5 V,		60	140	
Fall-Time	tf	Rg = 6 Ω		50	60	
Total Gate Charge	Qg	V_{DS} = 10 V,		47	60	nc
Gate-Source Charge	Qgs	V_{GS} = 4.5 V,		6		
Gate-Drain Charge	Qgd	I_D = 6 A		8		

Typical Performance Characteristics

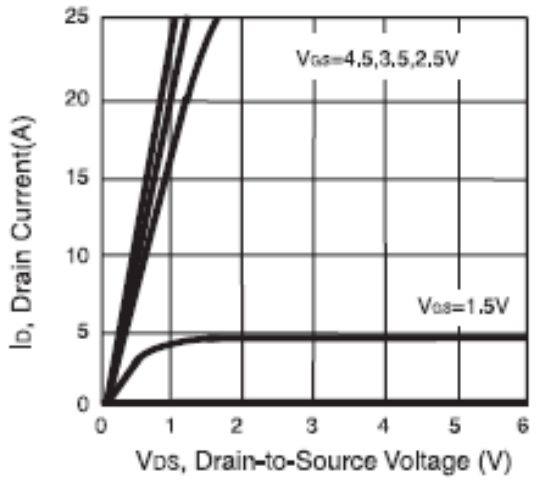


Figure 1. Output Characteristics

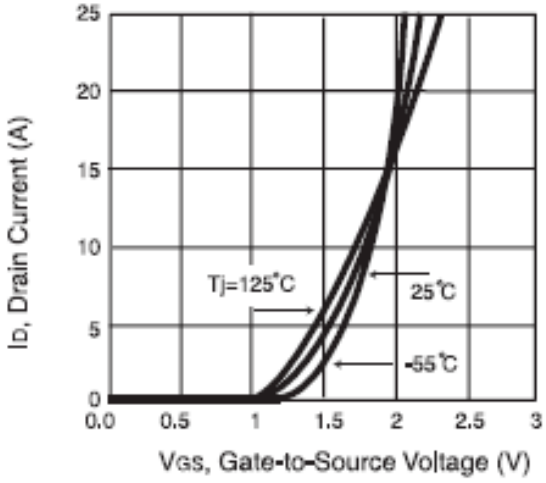


Figure 2. Transfer Characteristics

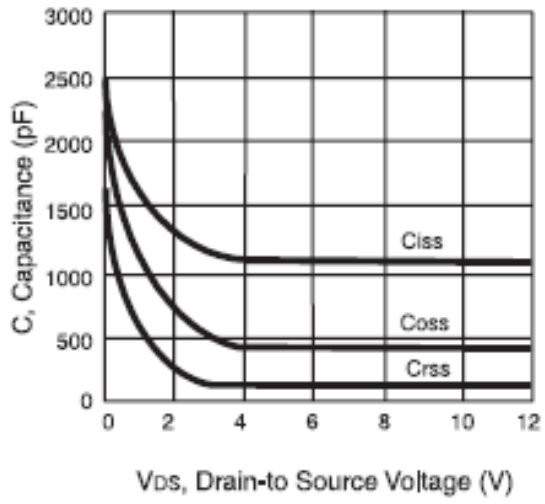


Figure 3. Capacitance

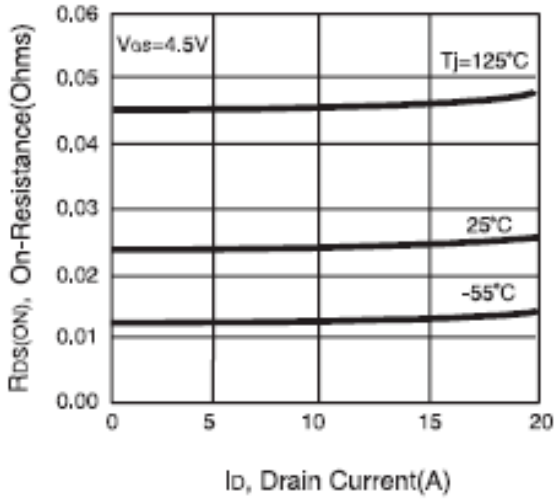


Figure 4. On-Resistance Variation with Drain Current and Temperature

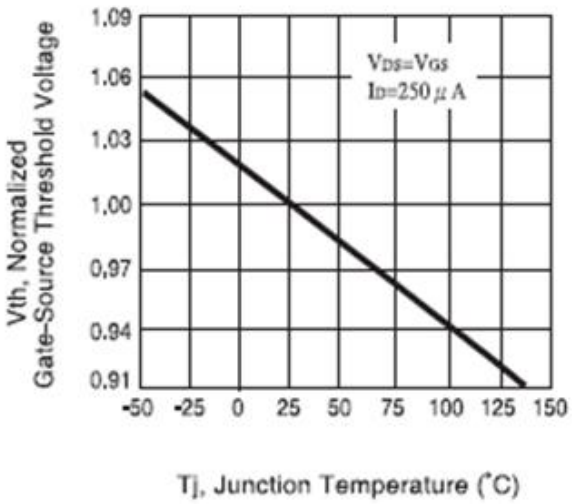


Figure 5. Gate Threshold Variation with Temperature

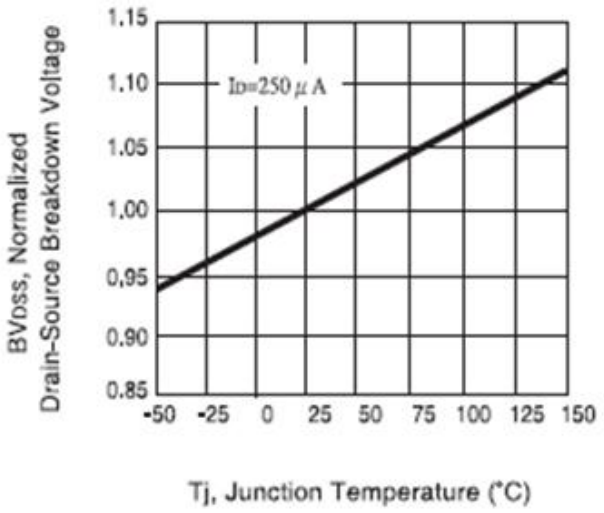


Figure 6. Breakdown Voltage Variation with Temperature

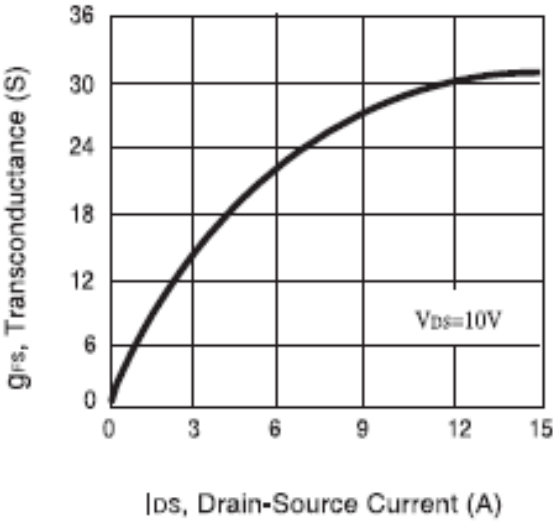


Figure 7. Transconductance Variation with Drain Current

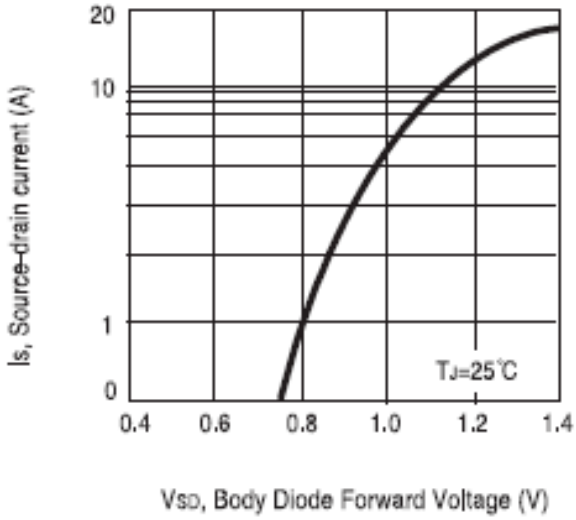


Figure 8. Body Diode Forward Voltage Variation with Source Current

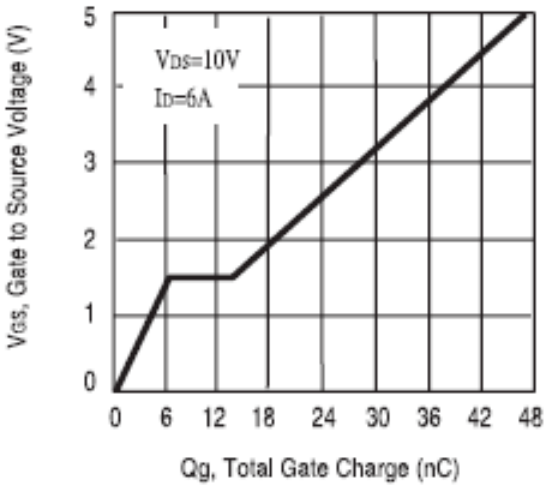


Figure 9. Gate Charge

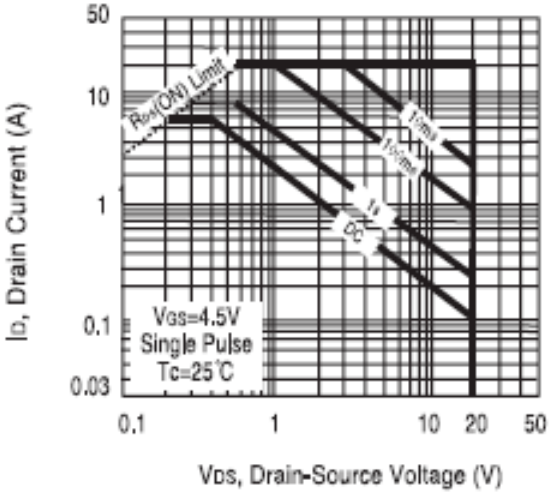


Figure 10. Maximum Safe Operating Area

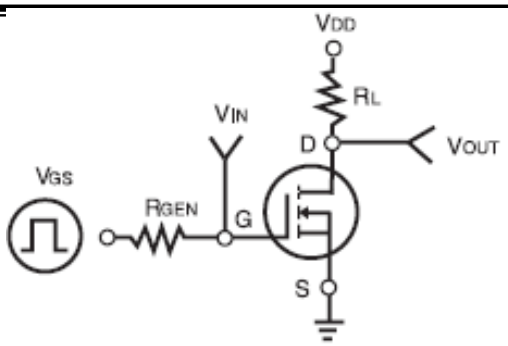


Figure 11. Switching Test Circuit

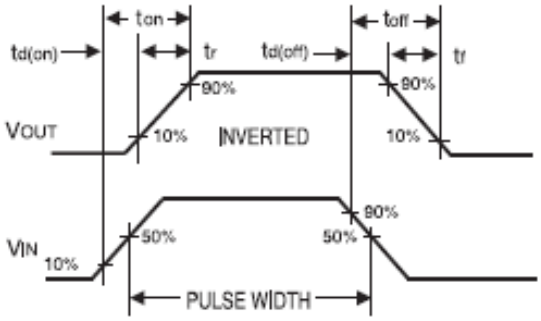


Figure 12. Switching Waveforms

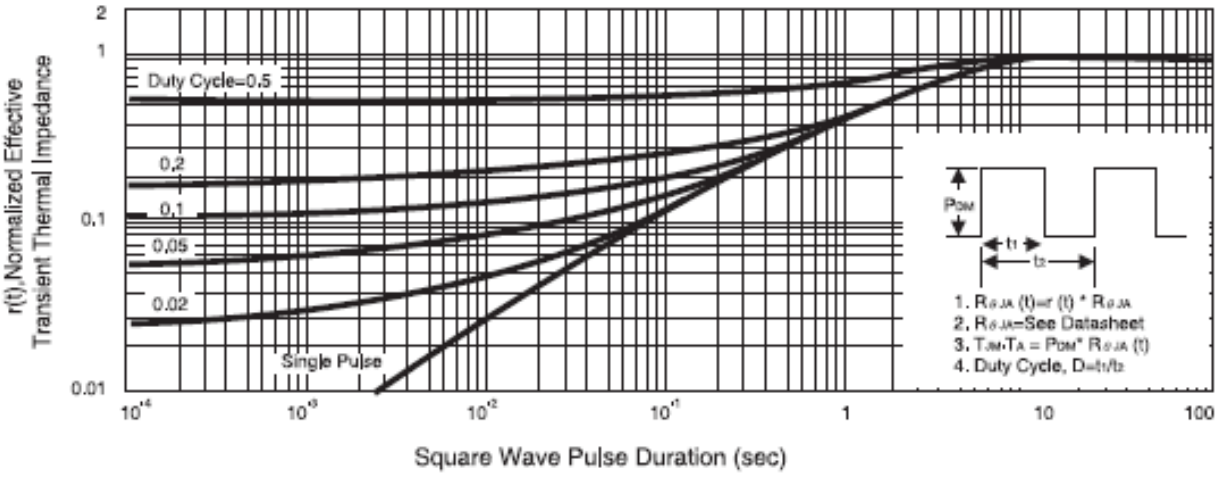
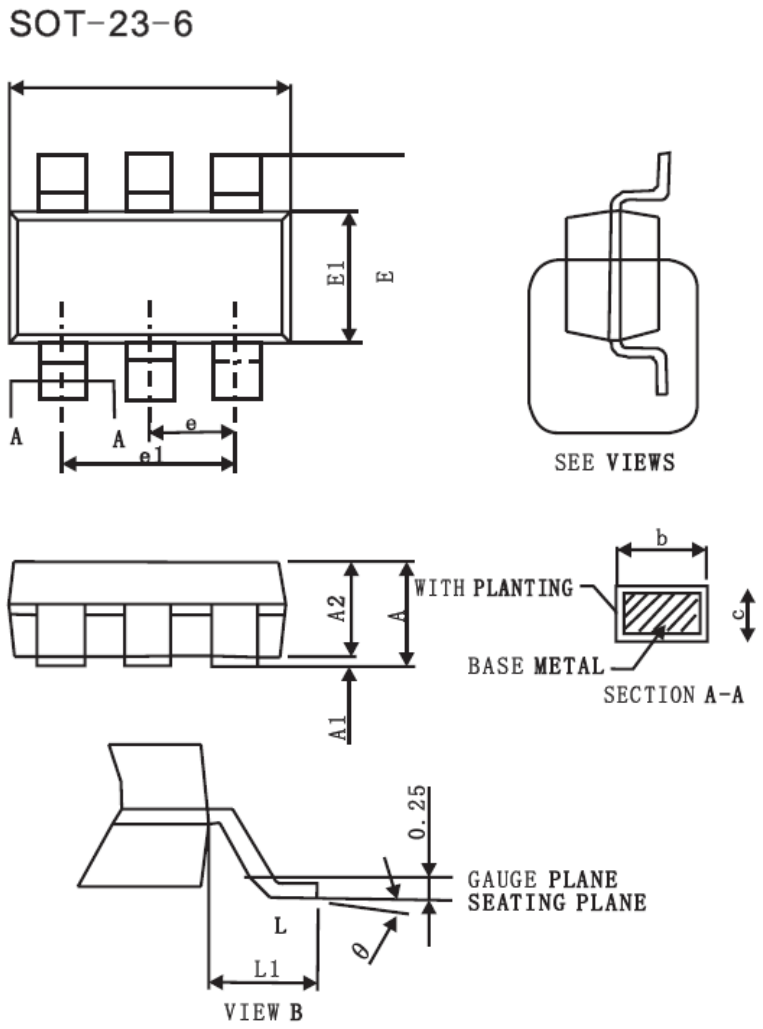


Figure 13. Normalized Thermal Transient Impedance Curve

Package Information

SOT23-6L



Symbol	A	A1	A2	b	c	D	E
Spec	1.20±0.25	0.10±0.05	1.10±0.2	0.40±0.1	0.15±0.0.7	2.90±0.1	2.80±0.2
Symbol	E11	e	e 1	L	L1	θ	
Spec	1.60±0.1	0.95BSC	1.90BSC	0.55±0.25	0.60REF	4°±4°	

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